

Description

The SQD19P06-60L_GE3 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

 $V_{DS} = -60V, I_{D} = -30A$

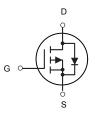
 $R_{DS(ON)} < 33m\Omega$ @ V_{GS} =-10V

Application

PWM applications

Load switch

Power management



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SQD19P06-60L_GE3	TO-252-2L	HXY MOSFET	2500

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit	
V _{DS}	Drain-Source Voltage (Vcs=0V)	-60	V	
V _G S	Gate-Source Voltage (V _{DS} =0V)	rce Voltage (V _{DS} =0V) ±20		
1-	Drain Current-Continuous(Tc=25℃)	-30	А	
l _D	Drain Current-Continuous(Tc=100°C)	-25.5	А	
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 1)	-144	А	
D.	Maximum Power Dissipation(T _C =25 ℃)	79	W	
P _D	Maximum Power Dissipation(T _C =100℃)	39.5	W	
Eas	Avalanche energy (Note 2)	196	mJ	
TJ, TSTG	Operating Junction and Storage Temperature Range	-55 To 175	${\mathbb C}$	



Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-60V, V _{GS} =0V			-1	μΑ
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.8	-2.5	V
g FS	Forward Transconductance	V _{DS} =-5V, I _D =-15A		35		S
		V _{GS} =-10V, I _D =-15A		29	33	mΩ
Rds(on)	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-10A		35	46	mΩ
Ciss	Input Capacitance			4026		pF
Coss	Output Capacitance	V _{DS} =-25V, V _{GS} =0V, f=1.0MHz		134		pF
Crss	Reverse Transfer Capacitance			98		pF
t _{d(on)}	Turn-on Delay Time			12.2		nS
tr	Turn-on Rise Time	V _{GS} =-10V, V _{DS} =-30V,		10		nS
t _{d(off)}	Turn-Off Delay Time	$R_L=1.5\Omega$, $R_{GEN}=3\Omega$		64		nS
t _f	Turn-Off Fall Time			14		nS
Qg	Total Gate Charge			68		nC
Qgs	Gate-Source Charge	V _{GS} =-10V, V _{DS} =-30V, I _D =-20A		10.5		nC
Q_{gd}	Gate-Drain Charge			13		nC
Isp	Source-Drain Current (Body Diode)				30	Α
Vsp	Forward on Voltage (Note 3)	V _G s=0V, Is=-15A			-1.2	V
t rr	Reverse Recovery Time	I _F =-20A, di/dt=100A/μs		26		ns
Qrr	Reverse Recovery Charge	I _F =-20A, di/dt=100A/μs		29		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature. Notes 2.E_{AS} condition: T_J =25°C, V_{DD} =40V, V_G =-10V, Rg=25 Ω , L=0.5mH. Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

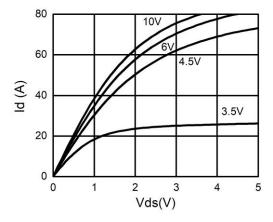


Figure 2. Transfer Characteristics

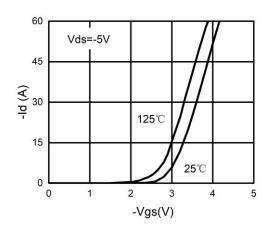


Figure 3. Power Dissipation

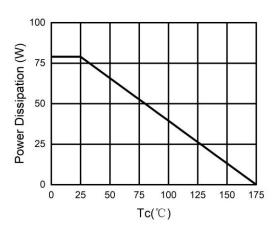


Figure 4. Drain Current

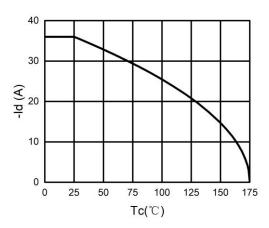


Figure 5. BV_{DSS} vs Junction Temperature

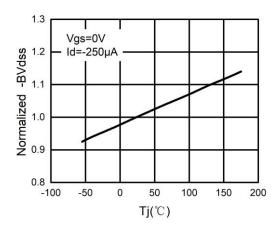


Figure 6. R_{DS(ON)} vs Junction Temperature

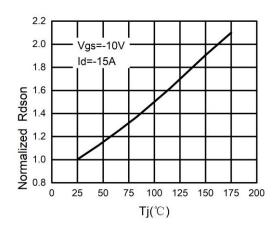




Figure 7. Gate Charge Waveforms

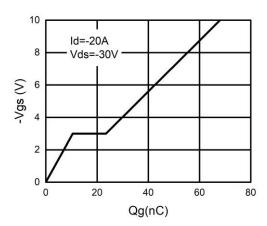


Figure 8. Capacitance

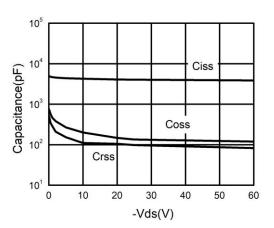


Figure 9. Body-Diode Characteristics

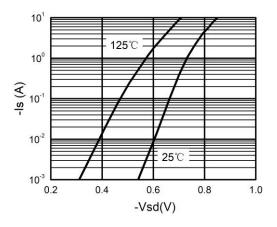
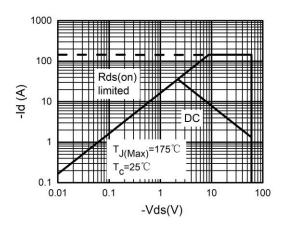
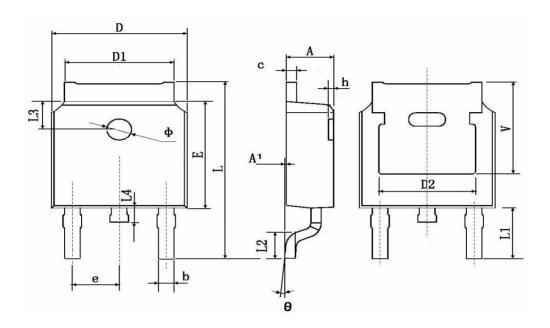


Figure 10. Maximum Safe Operating Area





TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
А	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.830 TYP.		0.190 TYP.			
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900 TYP.		0.114 TYP.			
L2	1.400	1.700	0.055	0.067		
L3	1.600	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350	TYP.	0.211 TYP.			



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